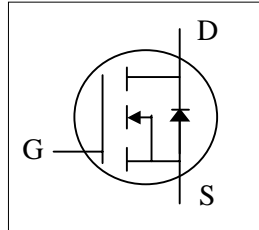




- ▼ Low Gate Charge
- ▼ Single Drive Requirement
- ▼ Surface Mount Package

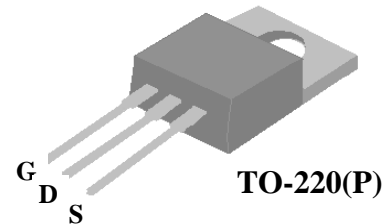
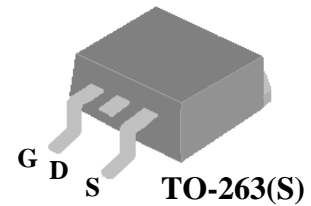


$BV_{DSS}$	60V
$R_{DS(ON)}$	18m $\Omega$
$I_D$	60A

## Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-263 package is widely preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters. The through-hole version (AP9972GP) are available for low-profile applications.



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 25$	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	60	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	38	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	230	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	89	W
	Linear Derating Factor	0.7	W/ $^\circ C$
$E_{AS}$	Single Pulse Avalanche Energy <sup>3</sup>	450	mJ
$I_{AR}$	Avalanche Current <sup>3</sup>	30	A
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

## Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	1.4	$^\circ C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	$^\circ C/W$



**Electrical Characteristics @T<sub>j</sub>=25°C(unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	-	-	V
ΔBV <sub>DSS</sub> /ΔT <sub>j</sub>	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	-	0.06	-	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =35A	-	-	18	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =25A	-	-	22	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	-	3	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =35A	-	55	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	10	uA
	Drain-Source Leakage Current (T <sub>j</sub> =150°C)	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V	-	-	25	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±25V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =35A	-	32	51	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =48V	-	8	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	20	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =30V	-	11	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =35A	-	58	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω, V <sub>GS</sub> =10V	-	45	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =0.86Ω	-	80	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	3170	5070	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =25V	-	280	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	230	-	pF
R <sub>g</sub>	Gate Resistance	f=1.0MHz	-	1.7	-	Ω

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =35A, V <sub>GS</sub> =0V	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time <sup>2</sup>	I <sub>S</sub> =35A, V <sub>GS</sub> =0V,	-	50	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	di/dt=100A/μs	-	48	-	nC

**Notes:**

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse width ≤300us , duty cycle ≤2%.
- 3.Starting T<sub>j</sub>=25°C , V<sub>DD</sub>=30V , L=1mH , R<sub>G</sub>=25Ω , I<sub>AS</sub>=30A.

THIS PRODUCT IS AN ELECTROSTATIC SENSITIVE, PLEASE HANDLE WITH CAUTION.

THIS PRODUCT HAS BEEN QUALIFIED FOR CONSUMER MARKET. APPLICATIONS OR USES AS CRITERIAL COMPONENT IN LIFE SUPPORT DEVICE OR SYSTEM ARE NOT AUTHORIZED.

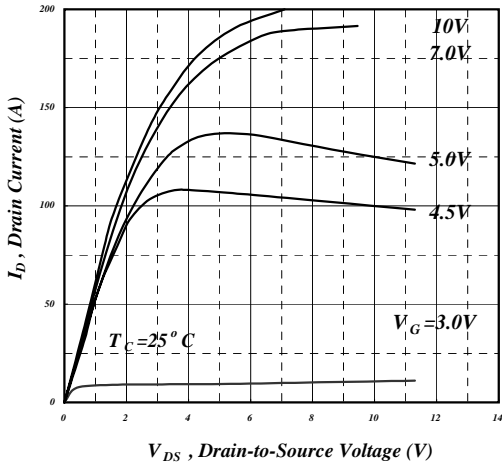


Fig 1. Typical Output Characteristics

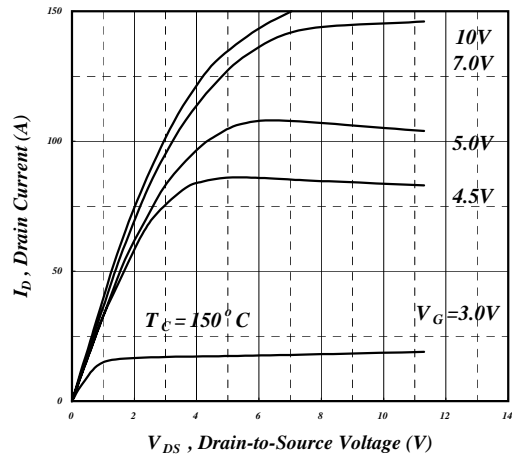


Fig 2. Typical Output Characteristics

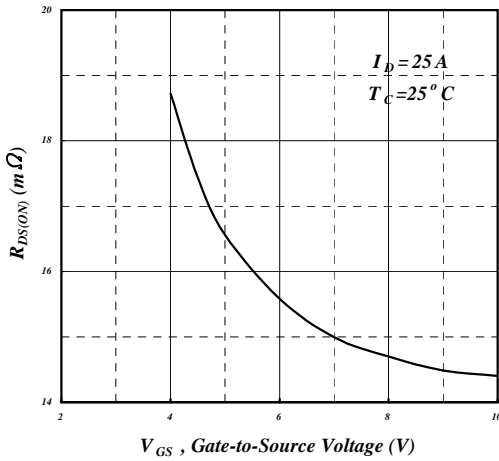


Fig 3. On-Resistance v.s. Gate Voltage

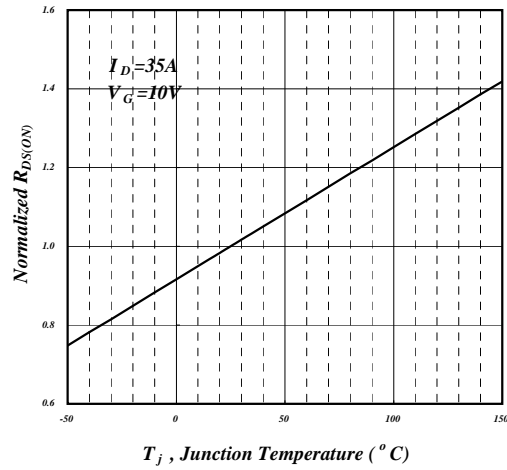


Fig 4. Normalized On-Resistance v.s. Junction Temperature

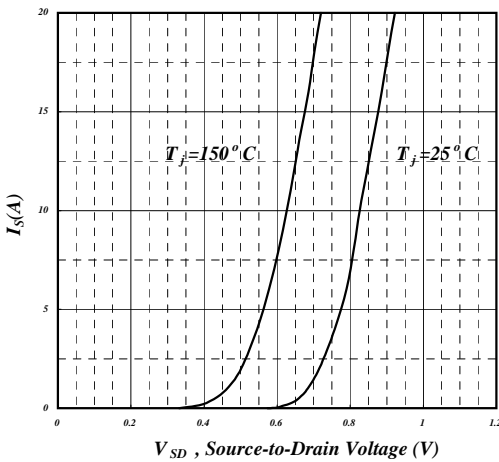


Fig 5. Forward Characteristic of Reverse Diode

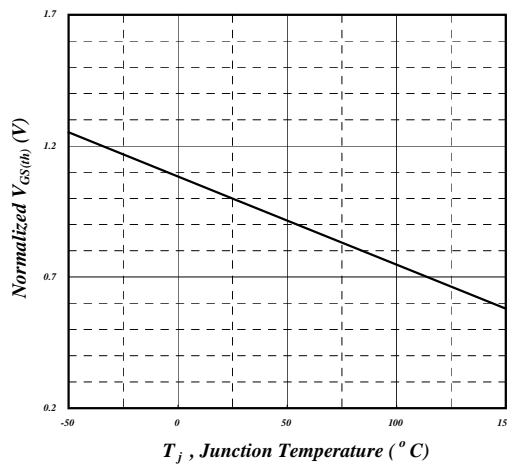


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



# AP9972GS/P

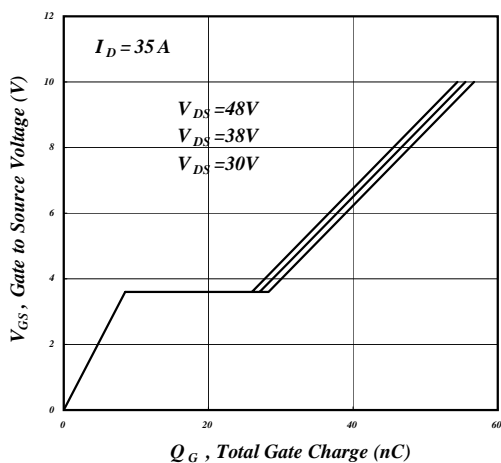


Fig 7. Gate Charge Characteristics

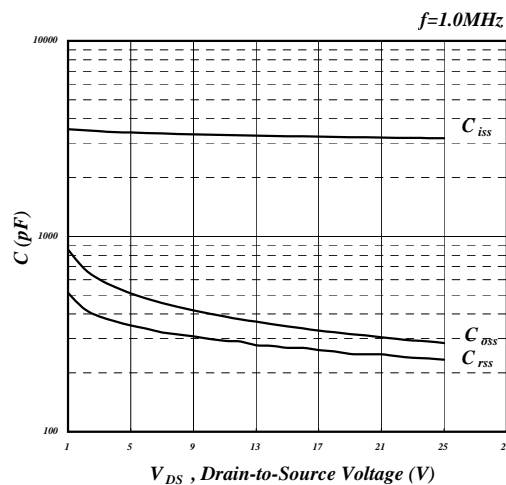


Fig 8. Typical Capacitance Characteristics

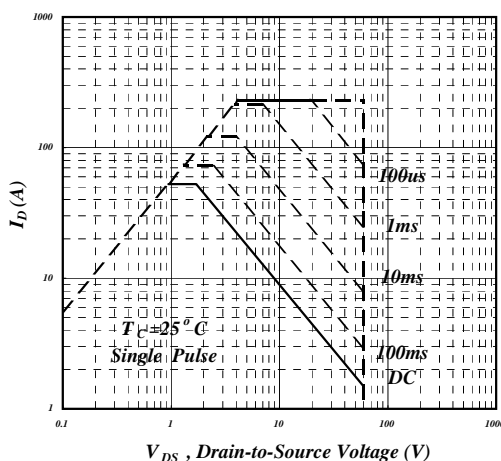


Fig 9. Maximum Safe Operating Area

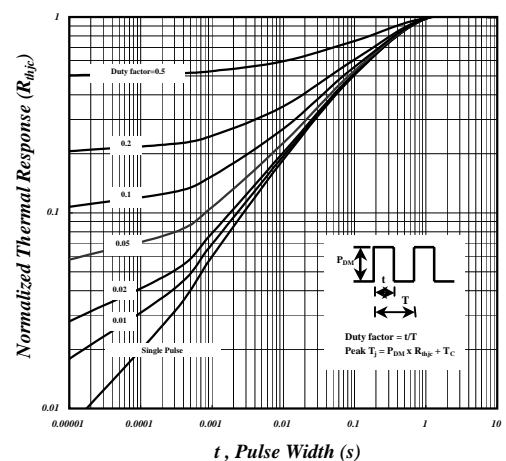


Fig 10. Effective Transient Thermal Impedance

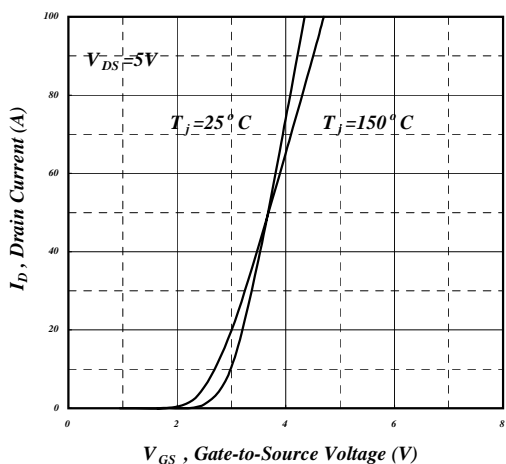


Fig 11. Transfer Characteristics

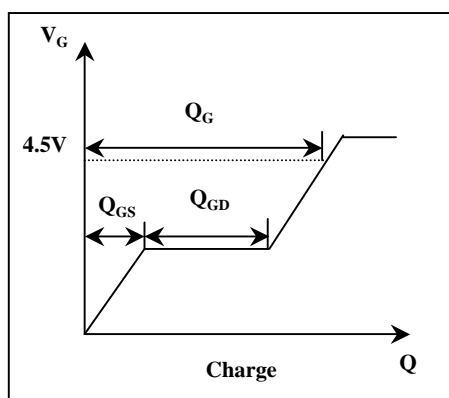
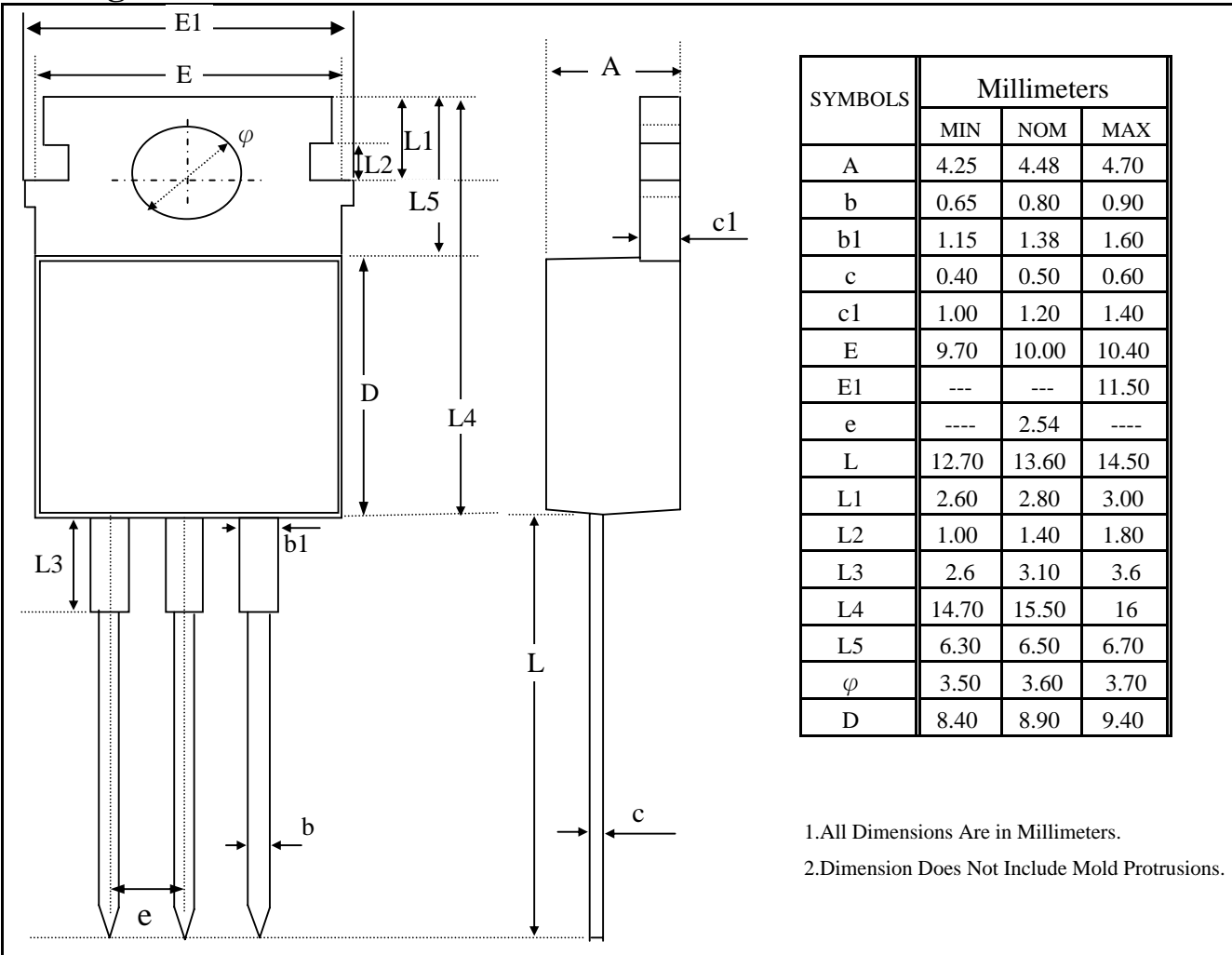


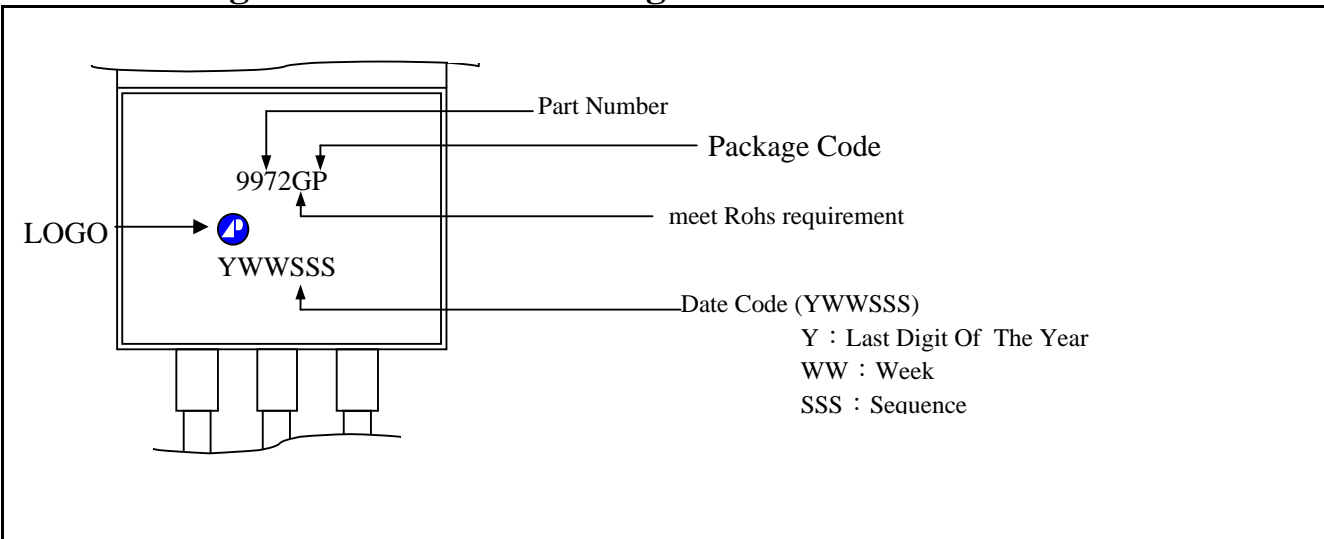
Fig 12. Gate Charge Waveform



### Package Outline : TO-220

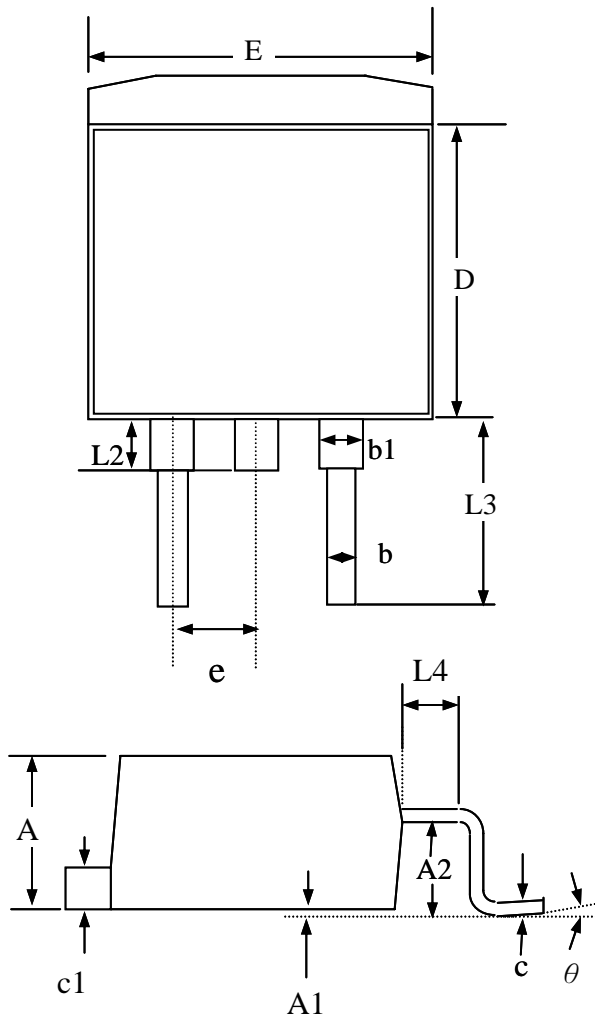


### Part Marking Information & Packing : TO-220





## Package Outline : TO-263



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	4.25	4.75	5.20
A1	0.00	0.15	0.30
A2	2.20	2.45	2.70
b	0.70	0.90	1.10
b1	1.07	1.27	1.47
c	0.30	0.45	0.60
c1	1.15	1.30	1.45
D	8.30	8.90	9.40
E	9.70	10.10	10.50
e	2.04	2.54	3.04
L2	-----	1.50	-----
L3	4.50	4.90	5.30
L4	-----	1.50	----

- 1.All Dimensions Are in Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.

## Part Marking Information & Packing : TO-263

